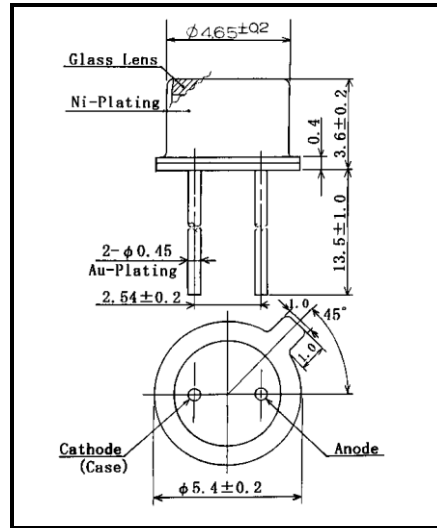
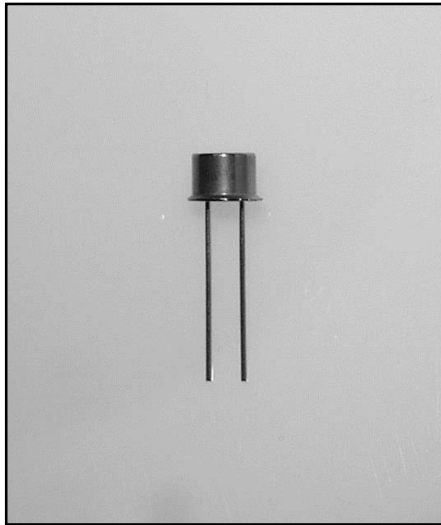


# LS853TM

# Infrared Emitting Diode



Dimensions (Unit:mm)

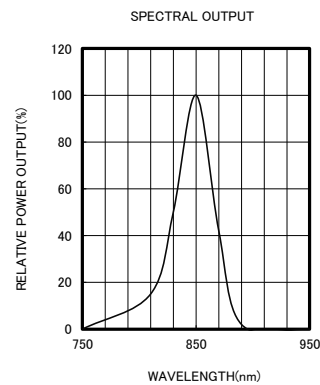
- FEATURES**
- Point-Source LED
  - High-output Power
  - High Reliability
  - Emitting Window Dia.  $\phi 50\mu\text{m}$
- APPLICATIONS**
- Optical Switches
  - Optical Instruments

## 1. ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

ITEM	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	80	mA
Forward Current (Pulse)*1	IFP	0.4	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	150	mW
Operating Temp.	Topr	-30 TO 100	°C
Storage Temp.	Tstg	-40 TO 125	°C
Junction Temp.	Tj	125	°C
Lead Soldering Temp.*2	Tls	260	°C

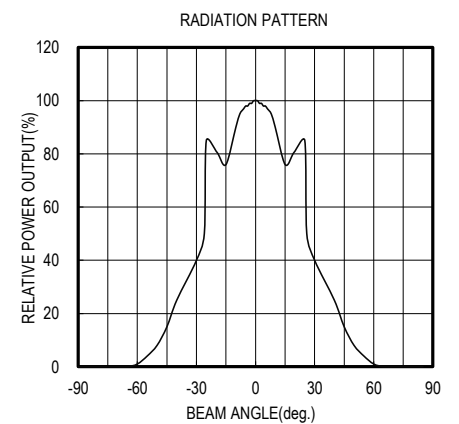
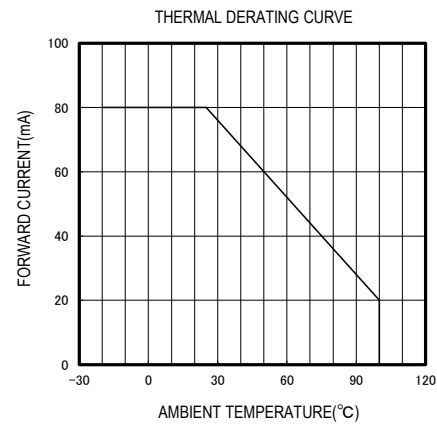
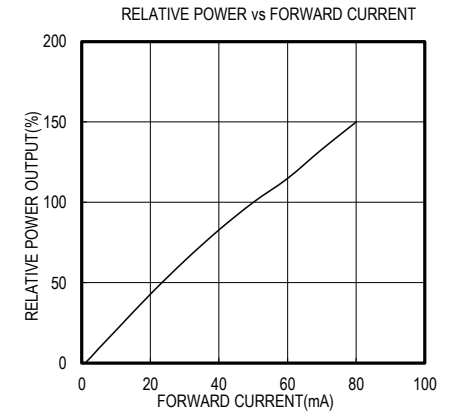
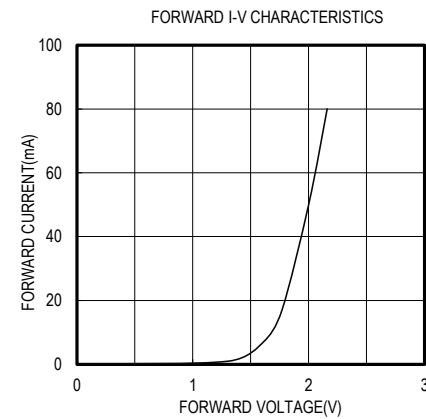
\*1: Tw=10uS, T=1mS

\*2: Time 5 Sec max, Position: Up to 3mm from the body



## 2. ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25°C)

ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=50mA		4.8		mW
Forward Voltage	VF	IF=50mA		2.0	2.4	V
Reverse Current	IR	VR=5V			10	A
Peak Wavelength	p	IF=50mA		850		nm
Spectral Line Half Width		IF=50mA		40		nm
Half Intensity Beam Angle		IF=50mA		$\pm 26$		deg.



OPTRANS

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